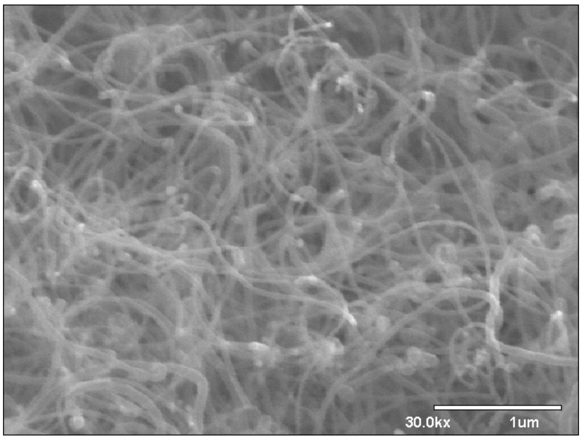

圖4-13 以MPCVD成長之奈米碳管SEM照片。

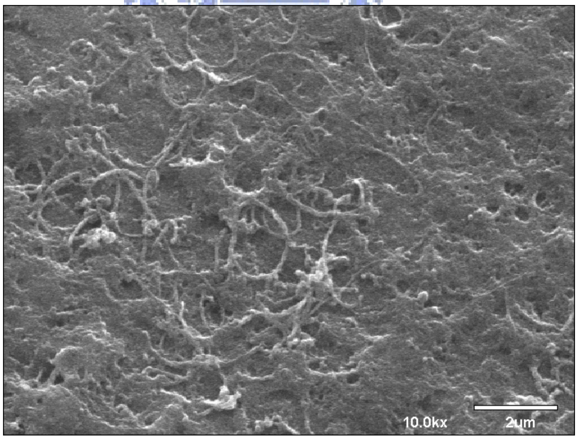

圖4-14 電泳沉積奈米碳管於鈦片表面之SEM照片。

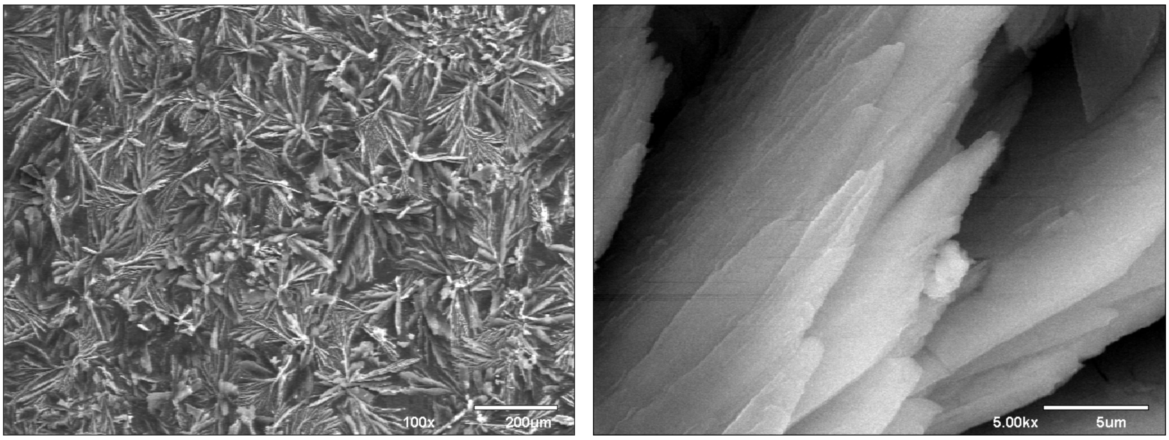

圖4-15 以3mA/cm^{2}電流密度、電解液25℃之沉積條件並經由300℃燒結之HAp/CNT鍍層SEM照片。

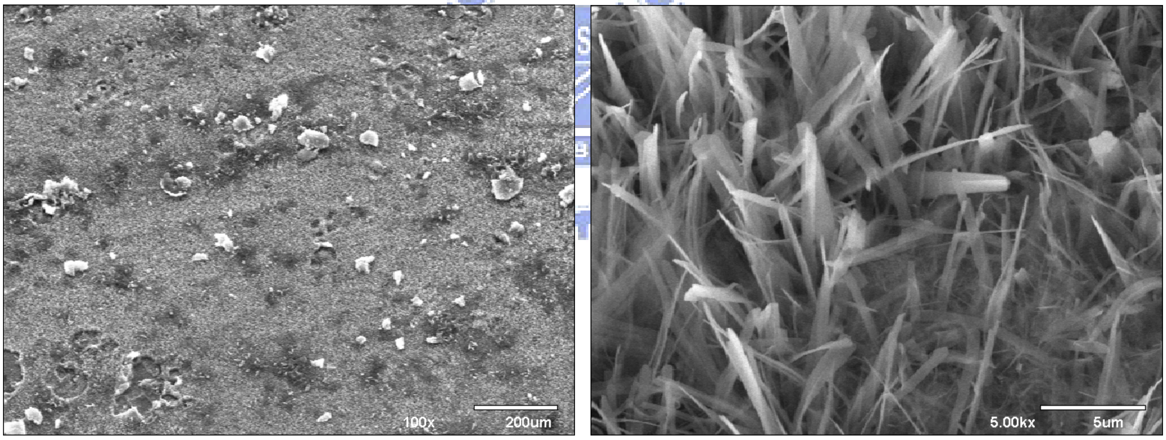

圖4-16 以3mA/cm^{2}電流密度、電解液65℃之沉積條件並經由300℃燒結之HAp/CNT鍍層SEM照片。

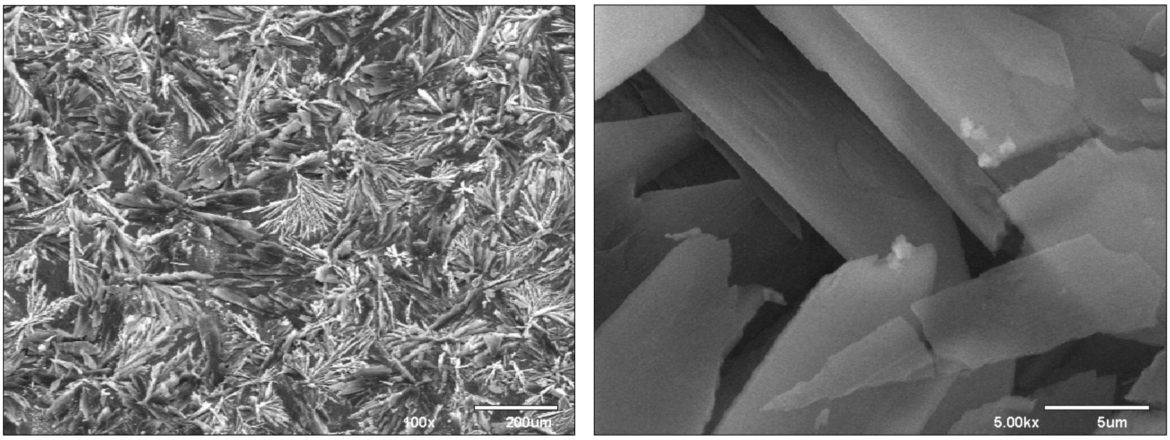

圖4-17 以3mA/cm^{2}電流密度、電解液25℃之沉積條件並經由300℃燒結之HAp/CNT鍍層SEM照片。

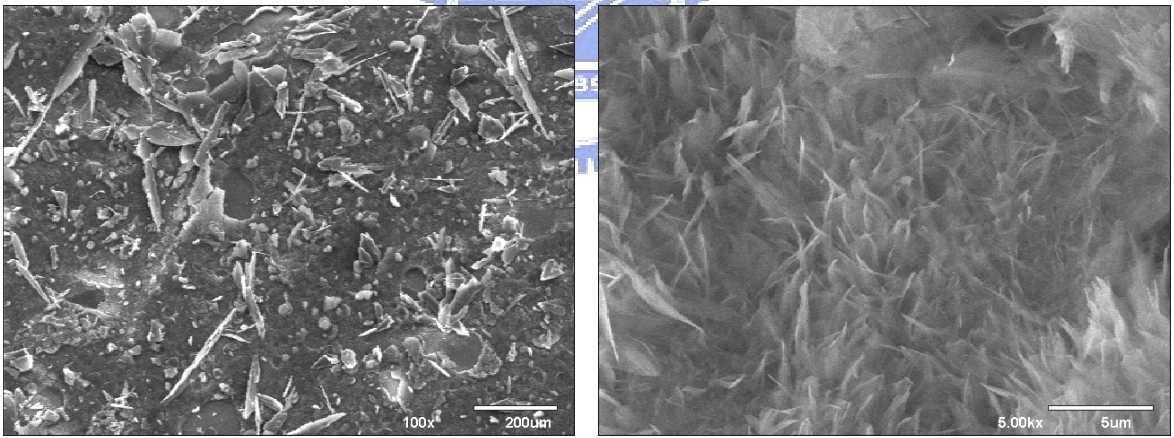

圖4-18 以3mA/cm^{2}電流密度、電解液65℃之沉積條件並經由300℃燒結之HAp/CNT鍍層SEM照片。

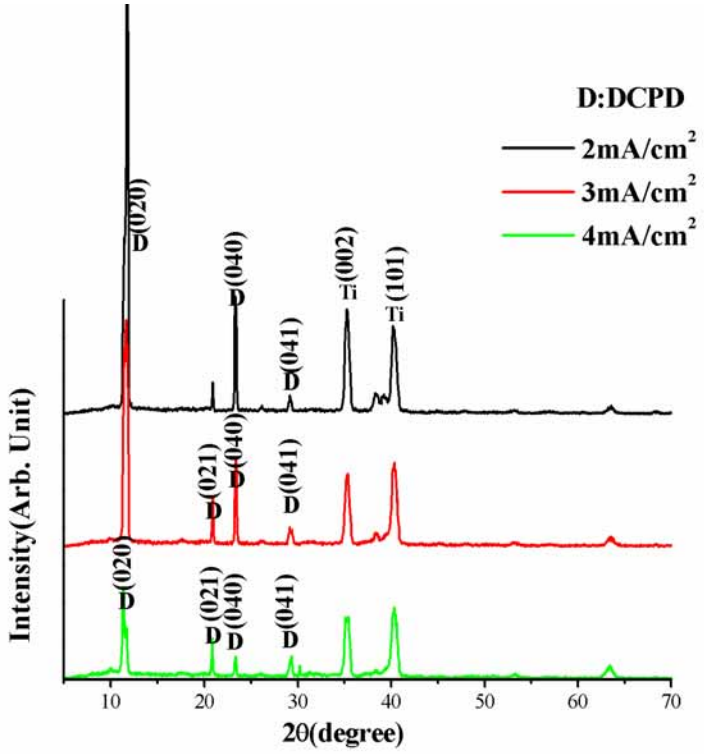

圖4-19 以各電流密度沉積、溶液未升溫、未經熱處理之單層HAp 鍍層X光繞射圖

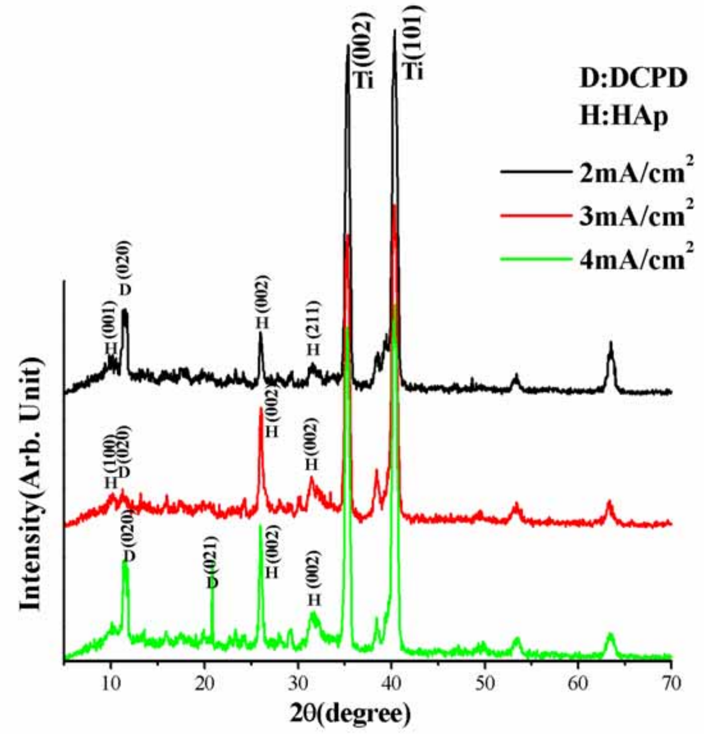

圖4-20 以各電流密度沉積、溶液未升溫、經熱處理之單層HAp 鍍層X光繞射圖

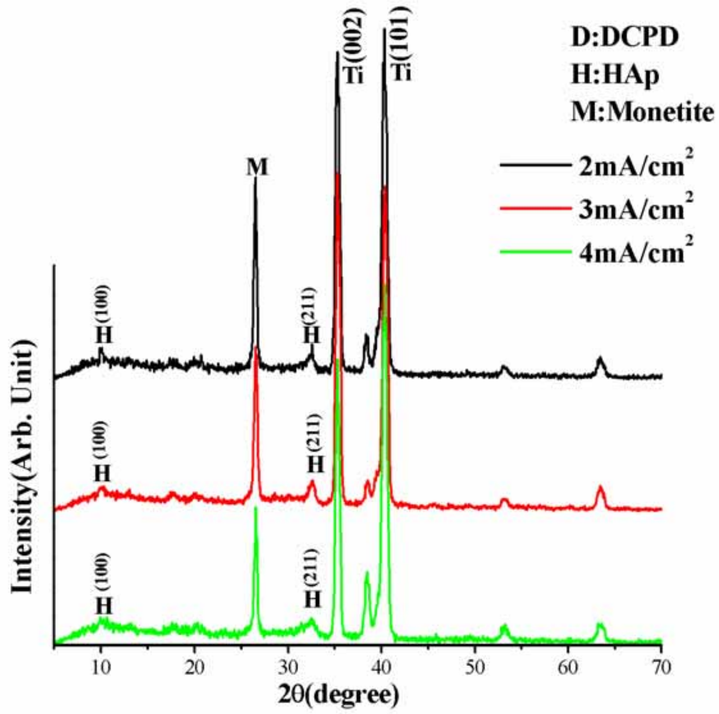

圖4-21 以各電流密度沉積、溶液升溫65℃、未經熱處理之單層HAp 鍍層X光繞射圖

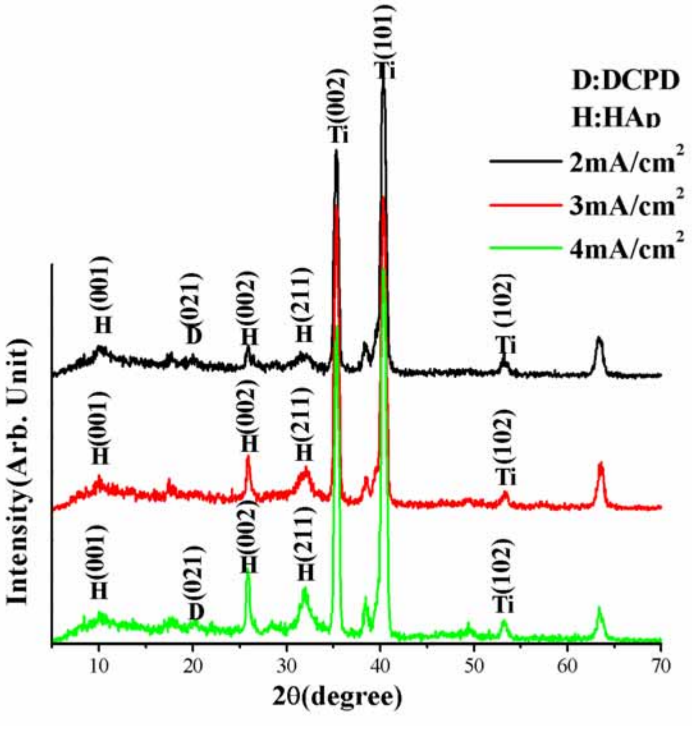

圖4-22 以各電流密度沉積、溶液升溫65℃、經熱處理之單層HAp 鍍層X光繞射圖

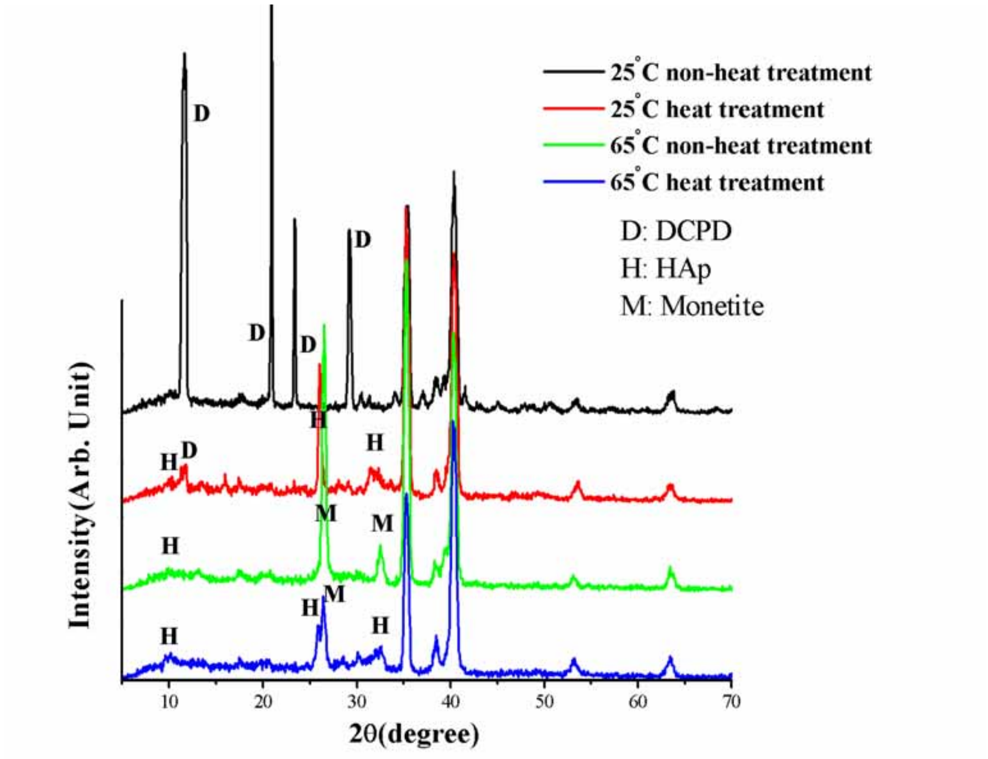

圖4-23 3mA/cm^{2}電流密度之沉積條件之HAp/CNTs 鍍層X光繞射圖

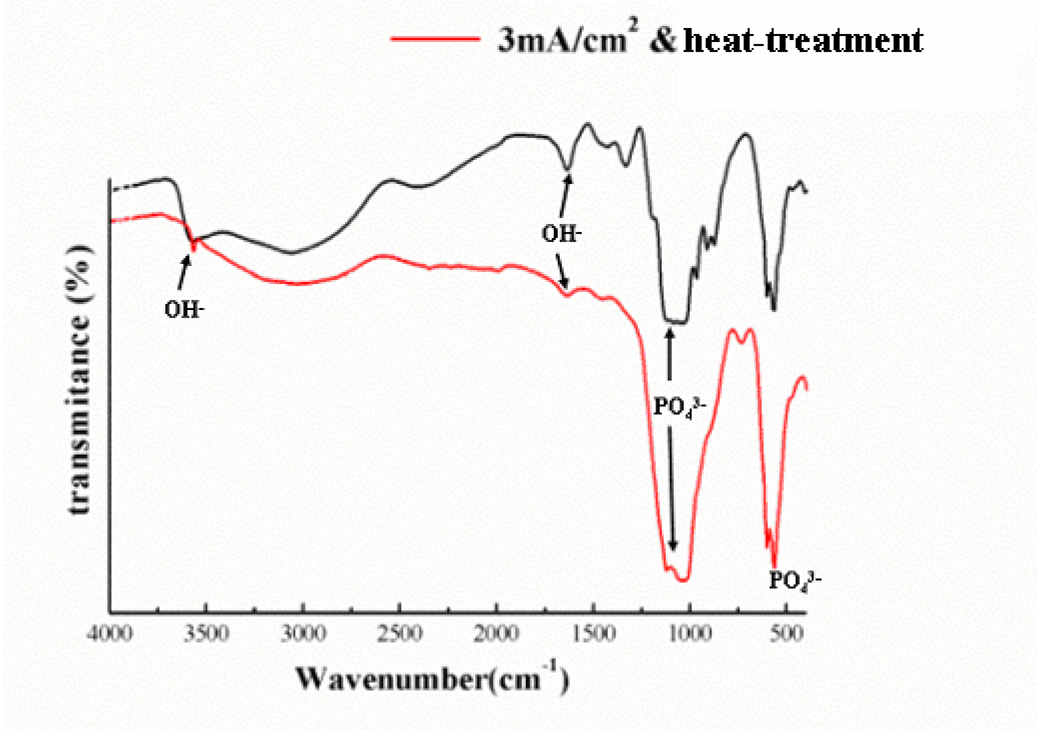

圖4-24 3mA/cm^{2}電流密度沉積條件之單層HAp 鍍層FTIR分析圖